Complementary Silicon Power Transistors

D44H Series (NPN), D45H Series (PNP)

These series of plastic, silicon NPN and PNP power transistors can be used as general purpose power amplification and switching such as output or driver stages in applications such as switching regulators, converters and power amplifiers.

Features

- Low Collector−Emitter Saturation Voltage
- Fast Switching Speeds
- Complementary Pairs Simplifies Designs
- These Devices are Pb−Free and are RoHS Compliant*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector−Emitter Voltage D44H8, D45H8 D44H11, D45H11	V_{CEO}	 60 80	Vdc
Emitter Base Voltage	V_{EB}	5.0	Vdc
Collector Current − Continuous	I_C	10	Adc
Collector Current − Peak (Note 1)	I_{CM}	20	Adc
Total Power Dissipation @ T_C = 25°C @ T_A = 25°C	P_D	 70 2.0	W
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

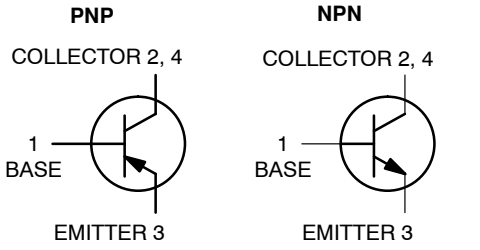
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.
1. Pulse Width ≤ 6.0 ms, Duty Cycle ≤ 50%.

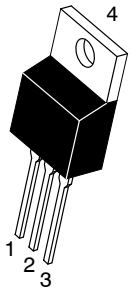
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction−to−Case	$R_{\theta JC}$	1.8	°C/W
Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$	62.5	°C/W
Maximum Lead Temperature for Soldering Purposes: 1/8″ from Case for 5 Seconds	T_L	275	°C

*For additional information on our Pb−Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

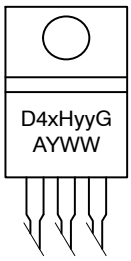
10 AMP COMPLEMENTARY SILICON POWER TRANSISTORS 60, 80 VOLTS





TO−220
CASE 221A
STYLE 1

MARKING DIAGRAM



D4xHyy = Device Code
x = 4 or 5
yy = 8 or 11
A = Assembly Location
Y = Year
WW = Work Week
G = Pb−Free Package

ORDERING INFORMATION

Device	Package	Shipping
D44H8G	TO−220 (Pb−Free)	50 Units/Rail
D44H11G	TO−220 (Pb−Free)	50 Units/Rail
D45H8G	TO−220 (Pb−Free)	50 Units/Rail
D45H11G	TO−220 (Pb−Free)	50 Units/Rail

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ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector−Emitter Sustaining Voltage (I_C = 30 mAdc, I_B = 0 Adc)	D44H8, D45H8 D44H11, D45H11	$V_{CEO(sus)}$	60 80	– –	– –	Vdc
Collector Cutoff Current (V_{CE} = Rated V_{CEO}, V_{BE} = 0)		I_{CES}	–	–	10	μA
Emitter Cutoff Current (V_{EB} = 5.0 Vdc)		I_{EBO}	–	–	10	μA
ON CHARACTERISTICS						
DC Current Gain (V_{CE} = 1.0 Vdc, I_C = 2.0 Adc) (V_{CE} = 1.0 Vdc, I_C = 4.0 Adc)		h_{FE}	 60 40	 – –	 – –	–
Collector−Emitter Saturation Voltage (I_C = 8.0 Adc, I_B = 0.4 Adc)		$V_{CE(sat)}$	–	–	1.0	Vdc
Base−Emitter Saturation Voltage (I_C = 8.0 Adc, I_B = 0.8 Adc)		$V_{BE(sat)}$	–	–	1.5	Vdc
DYNAMIC CHARACTERISTICS						
Collector Capacitance (V_{CB} = 10 Vdc, f_{test} = 1.0 MHz)	D44H Series D45H Series	C_{cb}	– –	90 160	– –	pF
Gain Bandwidth Product (I_C = 0.5 Adc, V_{CE} = 10 Vdc, f = 20 MHz)	D44H Series D45H Series	f_T	– –	50 40	– –	MHz
SWITCHING TIMES						
Delay and Rise Times (I_C = 5.0 Adc, I_{B1} = 0.5 Adc)	D44H Series D45H Series	$t_d + t_r$	– –	300 135	– –	ns
Storage Time (I_C = 5.0 Adc, I_{B1} = I_{B2} = 0.5 Adc)	D44H Series D45H Series	t_s	– –	500 500	– –	ns
Fall Time (I_C = 5.0 Adc, I_{B1} = 102 = 0.5 Adc)	D44H Series D45H Series	t_f	– –	140 100	– –	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

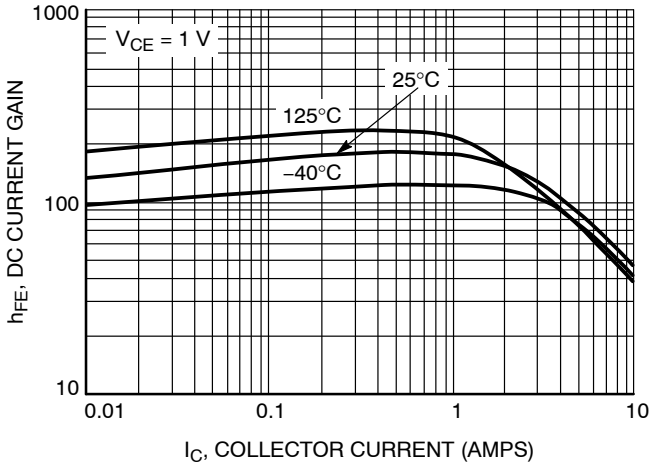


Figure 1. D44H11 DC Current Gain

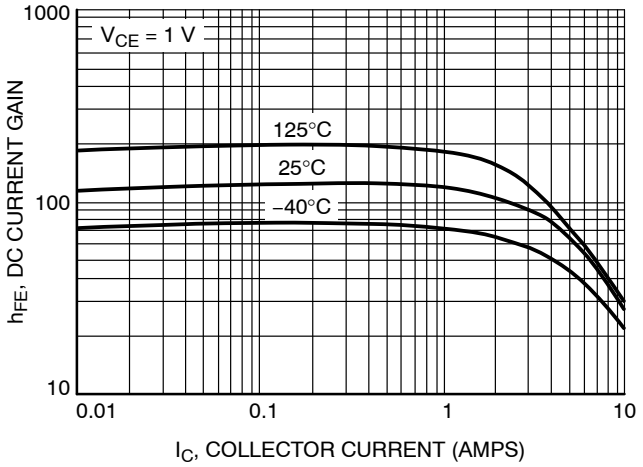


Figure 2. D45H11 DC Current Gain

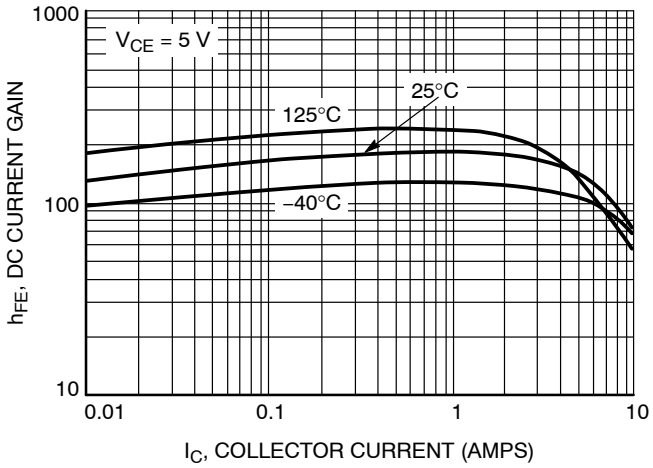


Figure 3. D44H11 DC Current Gain

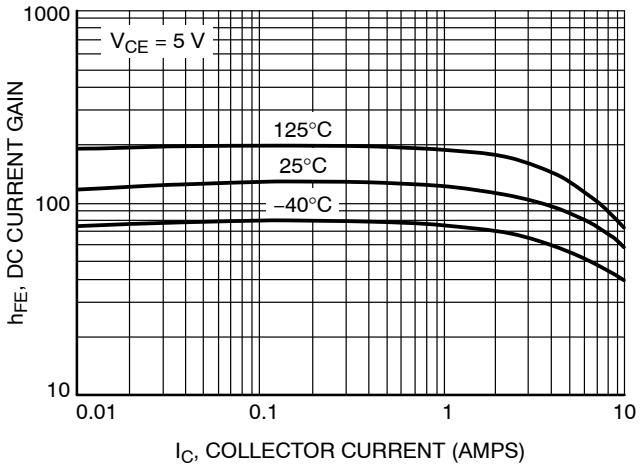


Figure 4. D45H11 DC Current Gain

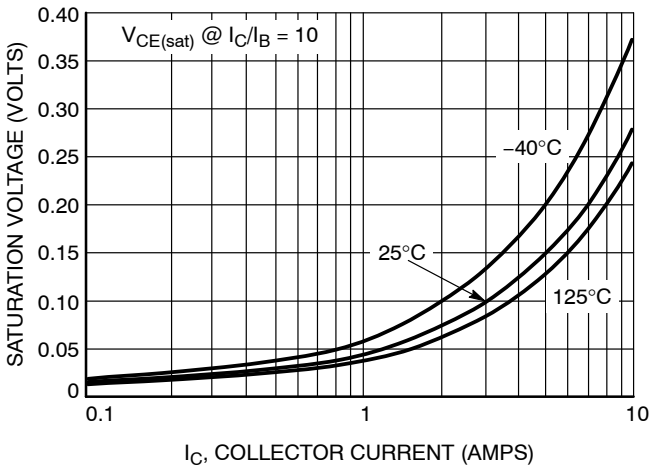


Figure 5. D44H11 ON−Voltage

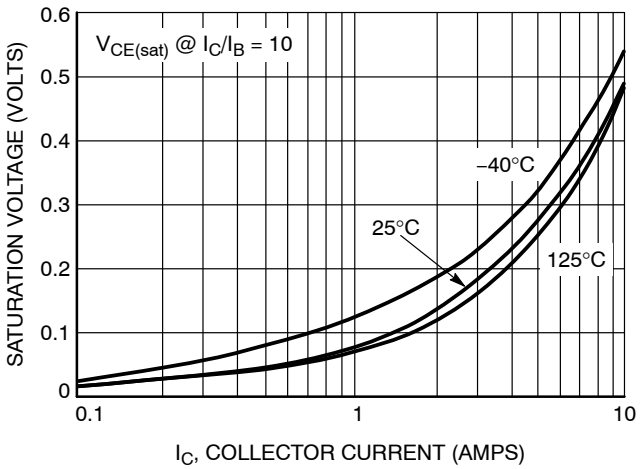


Figure 6. D45H11 ON−Voltage

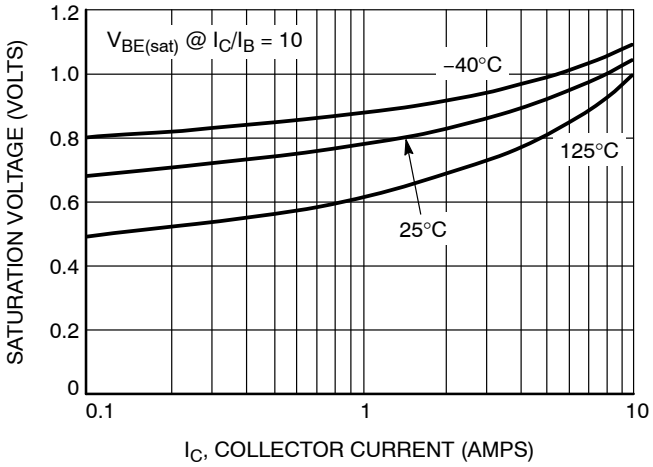


Figure 7. D44H11 ON−Voltage

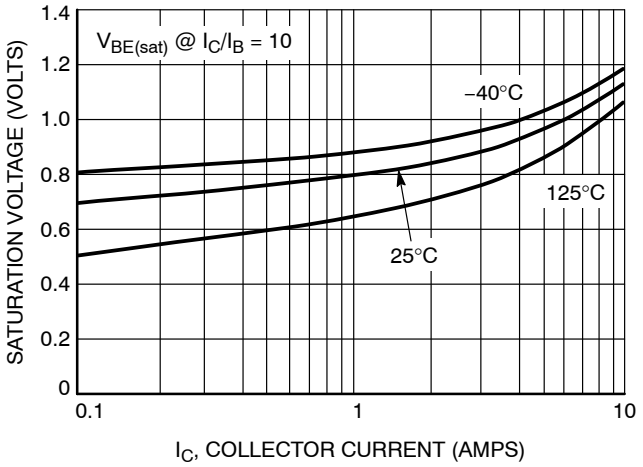


Figure 8. D45H11 ON−Voltage

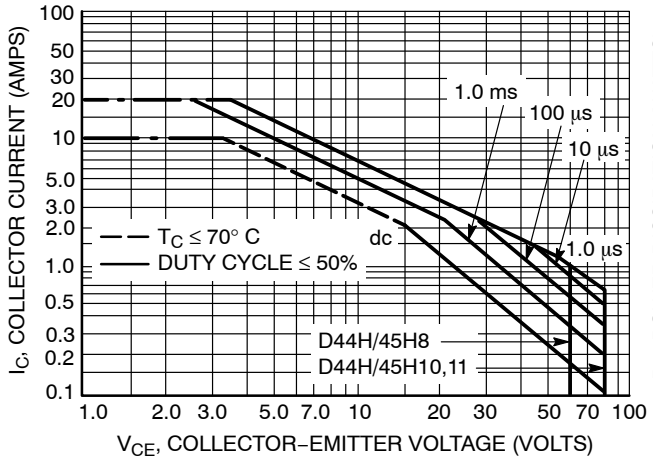


Figure 9. Maximum Rated Forward Bias Safe Operating Area

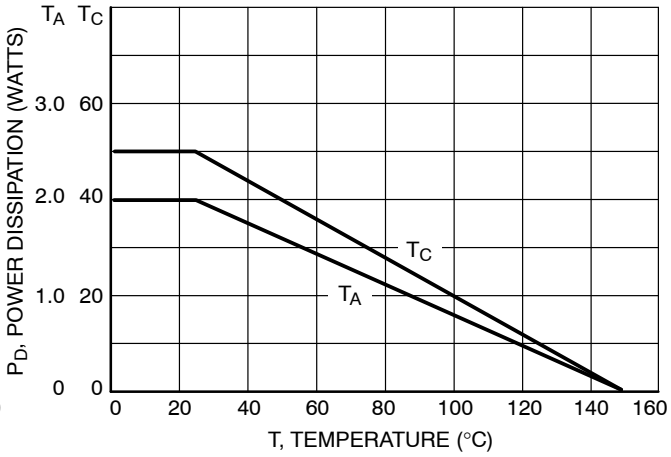


Figure 10. Power Derating

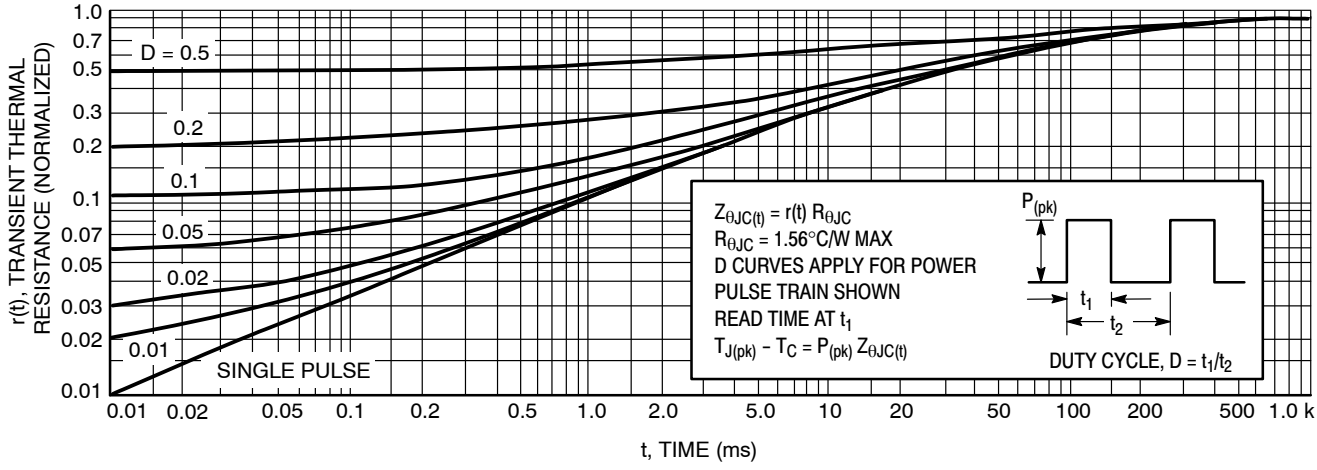
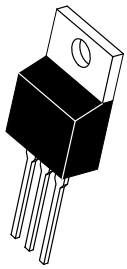


Figure 11. Thermal Response

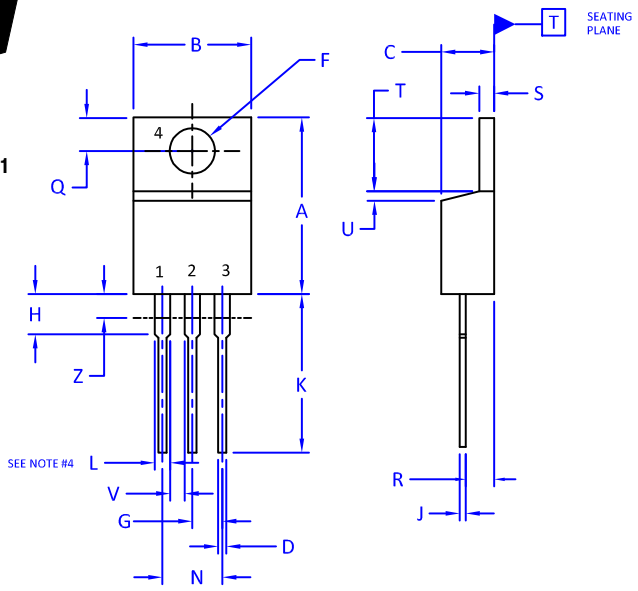
MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

TO−220
CASE 221A
ISSUE AK

DATE 13 JAN 2022



SCALE 1:1



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 2009.
2. CONTROLLING DIMENSION: INCHES
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.
4. MAX WIDTH FOR F102 DEVICE = 1.35MM

	INCHES		MILLIMETERS	
DIM	MIN.	MAX.	MIN.	MAX.
A	0.570	0.620	14.48	15.75
B	0.380	0.415	9.66	10.53
C	0.160	0.190	4.07	4.83
D	0.025	0.038	0.64	0.96
F	0.142	0.161	3.60	4.09
G	0.095	0.105	2.42	2.66
H	0.110	0.161	2.80	4.10
J	0.014	0.024	0.36	0.61
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.41
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	----	1.15	---
Z	----	0.080	---	2.04

STYLE 1:
PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 2:
PIN 1. BASE
2. EMITTER
3. COLLECTOR
4. EMITTER

STYLE 3:
PIN 1. CATHODE
2. ANODE
3. GATE
4. ANODE

STYLE 4:
PIN 1. MAIN TERMINAL 1
2. MAIN TERMINAL 2
3. GATE
4. MAIN TERMINAL 2

STYLE 5:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

STYLE 6:
PIN 1. ANODE
2. CATHODE
3. ANODE
4. CATHODE

STYLE 7:
PIN 1. CATHODE
2. ANODE
3. CATHODE
4. ANODE

STYLE 8:
PIN 1. CATHODE
2. ANODE
3. EXTERNAL TRIP/DELAY
4. ANODE

STYLE 9:
PIN 1. GATE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 10:
PIN 1. GATE
2. SOURCE
3. DRAIN
4. SOURCE

STYLE 11:
PIN 1. DRAIN
2. SOURCE
3. GATE
4. SOURCE

STYLE 12:
PIN 1. MAIN TERMINAL 1
2. MAIN TERMINAL 2
3. GATE
4. NOT CONNECTED

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DESCRIPTION:	**TO−220**	**PAGE 1 OF 1**

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